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Subject

Radiation Report on 54AC540LMQB SMEX Part No. 5962-87695012A Control No. 1405 Interoffice Memorandum

PPM-92-062

Date

Pebruary 14, 1992

Location

Lanham

Telephone

731-8954

Location

Lanham

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A radiation evaluation was performed on the 54AC540LMQB to determine the total dose tolerance of these parts. A brief summary of the test results is provided below. For detailed information, refer to Tables I through IV and Figure 1.

The total dose testing was performed using a cobalt-60 gamma ray source. During the radiation testing, eight parts were irradiated under bias (see Figure 1 for bias configuration), and two parts were used as control samples. The total dose radiation steps were 10, 20, 30, 50, 75, and 100 krads*. After 100 krads, the parts were annealed under bias at 25°C for 168 hours. After this annealing, the parts were irradiated to 200 and 300 krads (cumulative). Finally, the parts were annealed under bias for 168 hours at 100°C. The dose rate was between 200 and 5,160 rads/hour, depending on the total dose level (see Table II for radiation schedule). After each radiation exposure and annealing treatment, the parts were electrically tested at 25°C according to the test conditions and the specification limits listed in Table III. These tests included two functional tests at 1 MHz after each radiation and annealing step.

All parts passed both functional tests on irradiation up to 300 krads and on subsequent annealing treatment under bias for 168 hours at 100°C. Also, all parts stayed within the specification limits for all parameters on irradiation up to 10 krads. However, at 20 krads, four parts exceeded the maximum specification limits of 160 uA for ICCH and ICCL with readings as high as 1.8 mA. In addition, two of these parts marginally exceeded the same specification limit for ICCZ and marginally exceeded the IOZH specification limit of 10 uA. further irradiation to 50 krads, five parts were exceeding the limits for these same parameters. The ICCH and ICCL readings increased to a maximum of 15 mA. The ICCZ readings approached 5 mA and IOZH readings were as high as 900 uA. After further irradiation to 100 krads, six parts were exceeding the limits for these same parameters as they continued to degrade. The ICCH readings reached 34 mA. In addition, five parts were marginally exceeding the specification limits for TPZH. After 168 hours of annealing at 25°C, the parts recovered slightly. However, six parts continued to fail one or more of the above tests. On continued irradiation to 200 krads, seven parts exceeded the specification limits for ICC and IOZ tests and one part did not meet the specification limits for VOH1 and VOH4. At 300 krads, more VOH failures were observed and all parts exceeded the

specification limits on various tests. However, after annealing the parts for 168 hours at 100°C, no VOH failures were observed, average ICC readings decreased significantly as only two parts exceeded the specification limit for the ICC and IOZ tests. Table IV provides the mean and standard deviation values for each parameter after each radiation exposure and annealing treatment. It also provides a summary of the functional test results after each radiation/annealing step.

Any further details about this evaluation can be obtained upon request. If you have any questions, please call me at (301)731-8954.

In this report, the term "rads" is used as an abbreviation for rads (Si).

TABLE I. Part Information

Generic Part Number:

54AC540LMOB

SMEX Common Buy

Part Number:

5962-87695012A

SMEX Common Buy

Control Number:

1405

Charge Number:

C90352

Manufacturer:

National Semiconductor Corp.

Lot Date Code:

9040A

Quantity Tested:

8

Serial Numbers of

Radiation Samples:

663, 664, 665, 666, 667, 668, 669, 670

Serial Number of

Control Sample:

661, 662

Part Function:

OCTAL BUFFER LINE DRIVER

Part Technology:

CMOS

Package Style:

20-pin LCC

TABLE II. Radiation Schedule for 54AC540LMQB

EVE	NTS	DATE
1)	Initial (Pre-Irradiation) Electrical Measurements	10/24/91
2)	10 KRAD IRRADIATION (500 rads/hour) POST 10 KRAD ELECTRICAL MEASUREMENT	12/05/91 12/06/91
3)	20 KRAD IRRADIATION (500 rads/hour) POST 20 KRAD ELECTRICAL MEASUREMENT	12/06/91 12/07/91
4)	30 KRAD IRRADIATION (210 rads/hour) POST 30 KRAD ELECTRICAL MEASUREMENT	12/07/91 12/09/91
5)	50 KRAD IRRADIATION (950 rads/hour) POST 50 KRAD ELECTRICAL MEASUREMENT	12/09/91 12/10/91
6)	75 KRAD IRRADIATION (1,220 rads/hour) POST 75 KRAD ELECTRICAL MEASUREMENT	12/10/91 12/11/91
7)	100 KRAD IRRADIATION (1,250 rads/hour) POST 100 KRAD ELECTRICAL MEASUREMENT	12/11/91 12/12/91
8)	24 HOURS ANNEALING AT 25°C POST 24 HOURS ELECTRICAL MEASUREMENT	12/12/91 12/13/91
9)	168 HOURS ANNEALING AT 25°C POST 168 HOURS ELECTRICAL MEASUREMENT	12/12/91 12/19/91
10)	200 KRAD IRRADIATION (5,130 rads/hour) POST 200 KRAD ELECTRICAL MEASUREMENT	12/19/9 1 12/20/91
11)	300 KRAD IRRADIATION (5,160 rads/hour) POST 300 KRAD ELECTRICAL MEASUREMENT	12/20/91 12/23/91
12)	168 HOURS ANNEALING AT +100°C POST ANNEALING ELECTRICAL MEASUREMENTS	12/23/91 12/30/91

Notes:

- All parts were radiated under bias at the cobalt-60 gamma ray facility at GSFC.
- All electrical measurements were performed off-site at +25°C.
- All Annealing steps were performed under bias except as noted.

Table III. Electrical Characteristics of 54AC540LMQB

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ARAMETER	vcc			ILONAL TESTS P		•===
**=====	====		VIH ====	CONDITIONS	PINS	LIMITS 8 +25C
UNCT #1	3.0V 5.5V	0.0v	3.0V 5.5V	FREQ = 1MHz FREQ = 1MHz	ALL I/O	VOL<1.00V , VOH>2.00
	L	DAD USS	ED <=	C IOH ==5.0mA C VREF= 1.5V C IOL =+5.0mA		
			0C P/	ARAMETRIC TEST	S PERFORMED	
PARAMETER	A C C	VIL Seese	VIH	CONDITIONS	PINS	LIMITS @ +25C
7 D H Z	3.0V 4.5V	0.90V 1.35V	2.10V 3.15V	LOAD = -50UA LOAD = -50UA	2 T U O 2 T U O	>2.90V / <5.50V
V 0 H 3 V 0 H 4	5.5V 3.0V	1.65V	3.65V	LDAD = -50VA LOAD = -4MA	0015 0015	>>.40V / <5.50V
V DHS V DH6	4-5V	1.35V 1.65V	3.15Y		ÖÜTŠ	>2.40V , <5.50V >3.70V , <5.50V
ÝĎĤŽ	5.5V	1.65V	3.85V	LUAD = -50MA	0012	>4.70V / <5.50V >3.85V / <5.50V
PARAMETER	YCC	YIL	_YIH_	CONDITIONS	2419	LIMITS @ +25C
V0C1	3.97	0.904	2.10V	LOAO = +50UA	2700	>0.00V / <0.10V
VOL2 VOL3	4.5V 5.5V	1.354	3.15V 3.85V	LOAD = +500A	2700 2700	>0.00V > <0.10V >0.00V > <0.10V
VOL4 VOL5	3.0V 4.5V 5.5V	0.90V	2.10v 3.15v	LOAD = +12MA LDAD = +24MA	DŪTŠ GUTS	>0.00V / <0.50v
VOL6 VOL7	5.5V 5.5V	1.65V	3.85V		āŭŤŠ	>0.00V , <0.50V >0.00V , <0.50V
PARAMETER	VCC	VIL	VIH	CUNDITIONS	ÖUTŠ Pins	>0.00V / <1.85V
114		0.00v	=====		33 B E	LIMITS 8 +25C
ĬĪĹ	5.2V 5.5V 5.5V	0.007	5.50V	VIN = 5.5V	INS Ins	> -1.0UA / <+1.0UA > -1.0UA / < 0.0UA
IOZH	5.5V 5.5V	0.000	5.50V 5.50V	VOUT = 5.5V VOUT = 0.0V	00TS 00TS	> 0.00Å / <+10.00
ICCH	5.58	0.000	5.50V 5.50V	VIN = 0.00 VIN = 5.50	včć včć	> 0.00A > <160_00,
1002	5.5V	Ď.ããý.	5.50v	VÎN = 5.5V	včč	> 0.00A

PARAMETER	VCC ====	VIL *===	¥1#	PINS	LIMITS 25C
TPHL_00	4.5V 4.5V	0.04	4.5V 4.5V	DN TO QN ON TO QN	> 1.0NS < 5.5NS > 1.0NS < 6.0NS
TPZH_EQ TPZL_EQ	4.5V 4.5V	0.0Y	4.5V	DE TO QN DE TO QN	> 1.0NS < 8.5NS > 1.0NS < 7.5NS
TPHZ_EQ	4.5V 4.5V	0.0V 0.0V	4.5V 4.5V	DE TO ON DE TO ON	> 1.0NS <10.5NS > 1.0NS < 8.0NS

⁽¹⁾ VIL & VIH WERE TESTED DURING THE VOL & VOH TESTS AS GO/NO GO . (2) THIS PROGRAM CHECKS FOR PROPER DUT ORIENTATION. (3) AC PARAMETERS ARE TESTED AT 4.5V ONLY

TABLE IV: Summary of Electrical Measurements After
Total Dose Exposures and Annealing for 54AC540LMQB 1/2/

				<u> </u>	Total Dose Exposure (TDE) (krads)										An	neal	TDE		(krads	3)	Anneal		
			0 10		20		30		50		100		168 hrs		200		300		168 hrs				
		Spec	Limits	(Pre	-Rad)			_	-		• •			ĺ	100	@ 2		20	•	300			00°C
Paramete	ers	min		mean		mean	sđ	mean	sđ	mean	ad	mean	ន៤	mean	εđ	mean		mean	a d	меал	sd	mean	
FUNC1 @	1 MHz	_		Pass	1	Pass		Pass	_	PABB		Pass		Pass		Pase		Pass		Pass		Pass	su
FUNC2 @	1 MHz			Vate		Pess		Pass		Pass		Pass		Pass	-	Pass		Pass		Pass		Pass	
V0.E_1HOV	v	2.9	5.5	2,99	0	2.99	0	2.99	0	2.99	0	2.99	0		0.01		0.01	 	0.34	2.35	0.65	2.99	0
VOH2_4.5V	<u>v</u>	4.4	5.5	4.49	0	4.49	0	4.49	0	4.49	0	4.49		/.						3.84		6.49	
VOH3_5.5V	V	5.4	5.5	5.49	0	5,49	0	5.49	0	5.49	0	5.49			0.01						0.65	5.49	
VOR4_3.0V	٧.	2.4	5.5	2.93	_ 0	2.93	0	2.93	D	2.93	a	2.93			0.01					2.18	0.72	2.92	
VOH5_4.5V	٧	3.7	5 .5	4.20	0.01	4,20	0.01	4.20	0.01	4.20		4,19		4.18		•••••••••••				3.52		4.17	
VOH6_5.5V	V	4.7	5.5	5.23	0.01	5.23	0.01	5.23	0.01	5.23					0.01					4.52		5.21	
VDH7_5.5V	V	3.85	5.5	4.91	0.01	4.93	0.01	4.93	0.01	4.93					0.02					4.32	0.92	4.89	
VOL1_3.0V		0	0.10	0	0	9	٥	. 0	D	0	0	Ġ	0	0	0	0	0	0	0	0	0	0	0
VOL2_4.5V	<u> </u>	0	0.10	0	_ 0	Ð	٥	0	D	0	0	D	0	D	0	0	0	0	0	0	0	0	0
VOL3_5.5V	V	0	0.10	9 :::	G	0	0	0	0	G	0	0	0	0	0	0	0	0	0	0	0	0	0
VOL4_3.0V	V	0	0.50	0.12	0	0.12	Ó	0.12	0	0.12	0	0.12	0	0.12	0	0.12	0	0.11	0	0.12	0.01	0.13	0.01
VOL5_4.5V		0	0.50	0.17	0	0.17	0.01	0.17	0.01	0.17	0.01	0.17	0.01	0.17	0.01	0.17	0.01	0.17	0.01	0.17	0.01	0.18	0.02
VOL6_5.5V	V_	0	0.50	0.15	0	0.15	D	0.15	0.01	0.15	0.01	0,15	0.01	0.15	0.01	0.15	0.01	0.15	0.01	0.16	0.01	0.16	0.01
VOL7_5.5V	V	0	1.65	0.33	0.01	0.33	0.01	0.33	0.01	0.32	0.01	0.32			0.01			0.33	0.01	0.33	0.01	0.34	0.03
IIH	uA	0	1.0	0	. 0	D	D	0.	0	Q	0	Q.	0	0	0	0	0	0	0	. 0	0	0	0
IIL	uА	-1.0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	-	0	0	0	D
10ZH_	uA	0	10	0.01	0.03	0.01	0.04	2.04	7.20	22:75	66.1	147.2	312.0	549,1	951.0	444.9	806.0	1111	1875	1802	2666	10.42	51.47
IOZL	uA	-10	0	0	O.	0	a	0.01	0.02	33.30	77.7	0.08	0.12	0.04	0.08	0.07	0.11	~0.01	0.15	-0.10	5.22	n na	0.03
ІССН	uA.	0	160	0.10	0.14	18.41	30.10	451.5	602.2	1426	1569	5297	5014	14738	12673	10758	10013	24716	21060	36586	26873	570 R	973 6
ICCL	uA	0	160	0.05	0.13	18.D9	30.04	408.2	554.6	1186	1320	3895	3556	10052	B497	6960	6565	15410	13501	22286	15638	435.8	894.5
ICCZ	uA	0	160	0.04	0.10	4.25	6,62	106.1	1 58. 8	374.2	452.7	1671	1646	5432	4677	3677	3 532			14042			

TABLE IV (Continued): Summary of Electrical Measurements After Total Dose Exposures and Annealing for 54AC540LMQB 1/2/

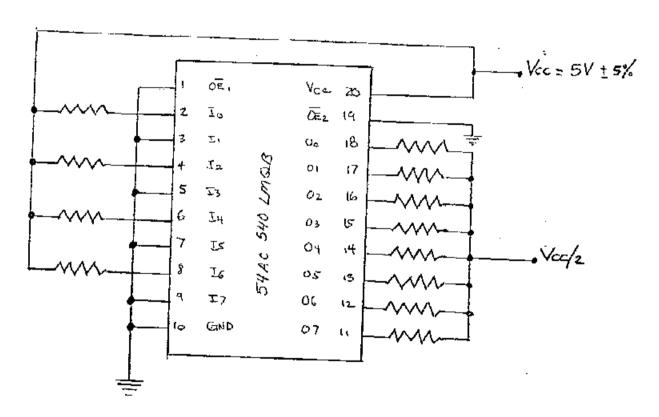
				Total			Dose	e Exp	osure	(TD	DE) (krads)				Anı	neal		TDE	(krads	3)	Anneal		
				0 (Pre-Rad)		10		.0 20		30		50		100		168 hrs		200		300		168 hrs	
		Spec	Limits]						ĺ				@ 25	5°C					1	00°C
Parameters		min_		mean		mean		mean		mean		mean		mean		mean	sd	mean sd		mean	вđ	mean	_
TPHL_DQ	n s	1.0	5.5	4.77	0.36	4.93	0.40	4.80	0.42	4.82	0.42	£.79	0.43	4 69	9E.0	5 74	O.AR	5. 36	0.50	5.07		5.31	
TPLH_DQ	ns	1.0	6.0	4.36	0.60	4.13	0.41	4.14	0.41	4.15	0.42	4.20	0.43	4 23	0.47	5 15	0.67	£ 9£	0.74	5.32	0.81	5.55	_
TPZH_BQ	nS	1.0	8.5	5.32	0.14	6.12	0.14	6.14	0.27	6 49	0.64	7 11	0.87	7 0/1	0 90	9 71	0.03		0 04	Ø.45	0.94	1	
TPZL_EQ	ns	1.0	7.5	6.84	0.20	6.72	0.20	6.56	0.21	6.70	0.23	6 71	0.23	6 70	0.28	7 60	0.36	7 66	0.94	7.73	0.19	7.69	
TPHZ_EQ	ns	1.0	10.5	4.84	1.00	4_61	0.77	4.41	0.82	4,38	0.82	4 34	0.80	4 21	0.73	5 23	0.90	5 02	0.88	1.74	0.87	5.70	
TPLZ_EQ	n s	1.0	8.0	4.95	0.14	5.60	0.13	5.52	0.13	5.54	0.12	5.55	0.13	5.51	0.15	6.41	0.14	6 39	0 18	5.31	0.20	5.00	

Notes:

^{1/} The mean and standard deviation values were calculated over the eight parts irradiated in this testing. The control samples remained constant throughout the testing and are not included in this table.

^{2/} Post 75 krads and post 24 hour annealing measurements at 25°C are not included in Table IV. This data is available upon request.

Figure 1. Radiation Bias Circuit for 54AC540LMQB



ALL RESISTORS ARE IKE 5% 1/4 W